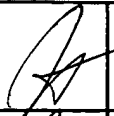
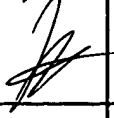

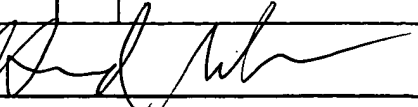


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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)					APPLICANT Lunn Tran et al.	
					FILING DATE Filed Herewith	GROUP
U.S. PATENT DOCUMENTS						
*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
	AA	5,045,899	09/03/91	Arimoto		
	AB	5,107,459	04/21/92	Chu et al.		
	AC	5,350,706	09/27/94	McElroy et al.		
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	AJ	5,747,844	05/05/98	Aoki et al.		
	AK	5,665,623	09/09/97	Liang et al.		
FOREIGN PATENT DOCUMENTS						
	Document Number	Date	Country	Class	Subclass	Translation
						Yes No
	AL	JP 03205868	09/09/91	Japan		Abs.
	AM					
	AN					
	AO					
	AP					
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	AS	M. Aoki et al., "Fully Self-Aligned 6F ¹ Cell Technology for Low Cost 1Gb DRAM", IEEE				
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*Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate		
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FOREIGN PATENT DOCUMENTS								
	Document Number	Date	Country	Class	Subclass	Translation		
						Yes	No	
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FOREIGN PATENT DOCUMENTS								
		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AM							
	AN							
	AO							
	AP							
	AQ							
OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)								
	AR		V. Mathews et al., <i>Dry O₂ High Pressure Field Oxidation for 0.25 μm Isolation Technology</i> .					
			SSDM '95 - Device and Process Technology, 2 pages.					
	AS		Fazen, et al., "A High-C Capacitor (20.4fF/μ ²) with Ultrathin CVD-Ta ₂ O ₅ films Deposited on Rugged Poly-Si for High Density DRAMs": 1992: 4 pps.					
	AT		Fazen et al., "A Highly Manufacturable Trench Isolation Process for Deep Submicron DRAMS," ©1993 IEEE, 4 pages.					
EXAMINER 				DATE CONSIDERED 9/17/07				
<p>*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.</p>								